Section I. (Amendments to the Specification)

Please replace paragraph [0006] with the following new replacement paragraph:

[0006] The deposition and/or processing of Ir-based electrodes is highly desirable based on the above-discussed advantages. Ir displays a resistivity 5.3 μΩ-cm at 20°C and IrO_2 is highly conducting with a reported resistivity of 100 μΩ-cm. The formation of IrO_2 occurs only at elevated temperatures (>550°C) in O_2 and is a superior material for the deposition of complex oxides for dielectric or ferroelectric capacitors. Further, during the high temperature CVD process for the growth of these capacitors, the formation of IrO_2 can be advantageous for limiting inter-diffusion, as for example by acting as a diffusion barrier to oxidation of conducting polysilicon vias or plugs. IrO_2 therefore is a material having many advantages in forming a robust, low-leakage electrode for reliable device fabrication.